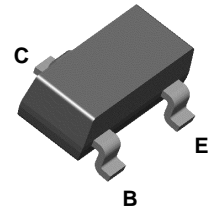


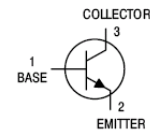
NPN General Purpose Amplifier

Features

- $I_C = 600\text{mA}$
- Epitaxial planar die construction.
- Ultra-small surface mount package.



Mark: 1B

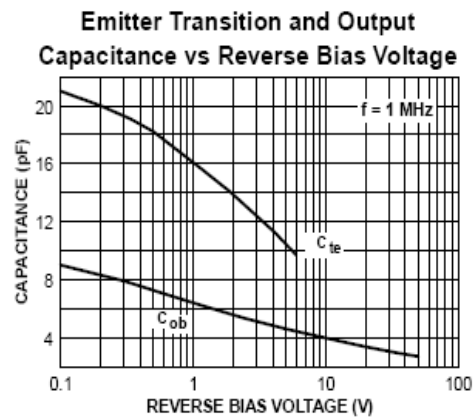
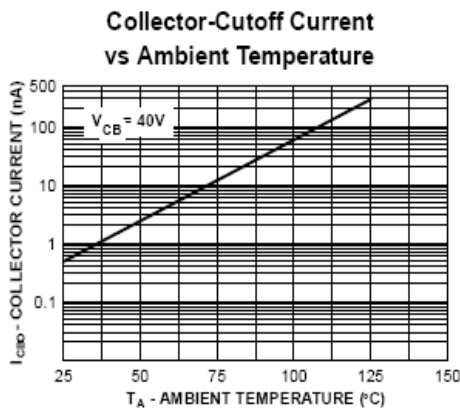
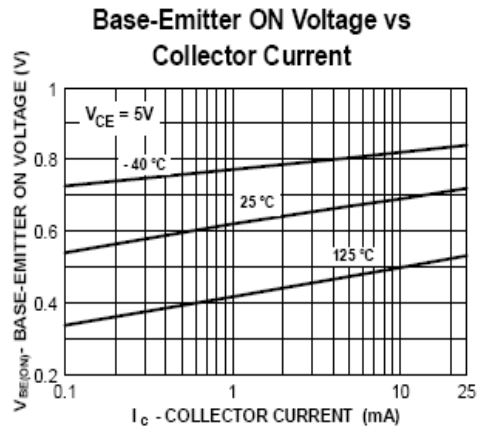
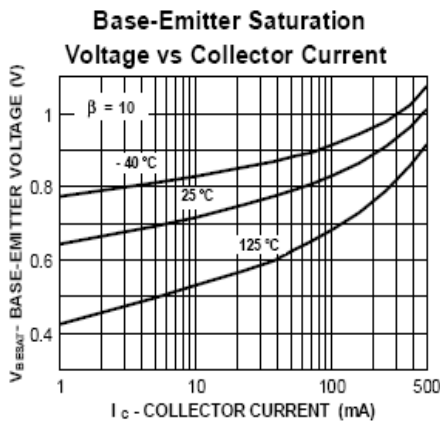
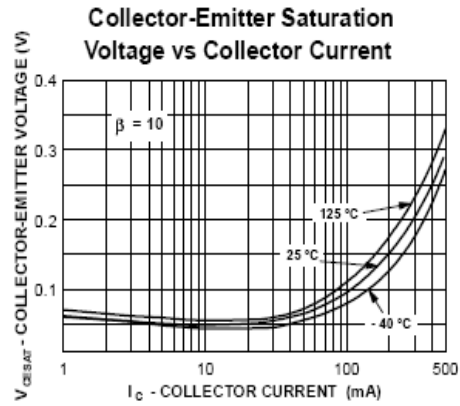
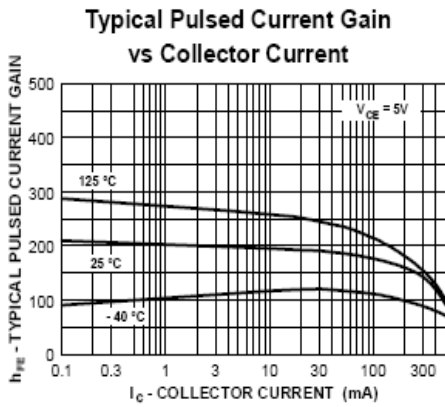


Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	60	V
V_{CEO}	Collector-Emitter Voltage	30	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current -Continuous	600	mA
P_C	Collector Dissipation	200	mW
T_j, T_{stg}	Junction and Storage Temperature	-55~150	°C

Electrical Characteristics

$T_A = 25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = 10\ \mu\text{A}, I_E = 0$	60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 10\text{mA}, I_B = 0$	30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = 10\ \mu\text{A}, I_C = 0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB} = 50\text{V}, I_E = 0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 3\text{V}, I_C = 0$			0.1	μA
DC current gain	h_{FE}	$V_{CE} = 10\text{V}, I_C = 10\text{mA}$	75			
		$V_{CE} = 10\text{V}, I_C = 150\text{mA}$	100		300	
		$V_{CE} = 10\text{V}, I_C = 500\text{mA}$	30			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 150\text{mA}, I_B = 15\text{mA}$			0.4	V
Base-emitter voltage	V_{BE}	$I_C = 150\text{mA}, I_B = 15\text{mA}$			1.3	V
Transition frequency	f_T	$V_{CE} = 20\text{V}, I_C = 20\text{mA}$	300			MHz
Collector Output Capacitance	C_{Ob}	$V_{CB} = 10\text{V}, I_E = 0$ $f = 100\text{KHz}$			8.0	PF



OUTLINE DRAWING

SOT-23

